

In the Claims:

The listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

1. (Original) A method of fabricating a light emitting device including a silicon carbide substrate having first and second opposing faces and a light emitting element on a first face of the <sup>SIC</sup>substrate, comprising:

directly etching the second face of the silicon carbide substrate utilizing an aqueous etch to remove a damaged portion of the substrate resulting from processing of the <sup>SIC</sup>substrate.

2. (Original) The method of Claim 1, wherein the damaged portion of the second face of the <sup>SIC</sup>silicon carbide substrate results from sawing the <sup>SIC</sup>substrate, lapping the <sup>SIC</sup>substrate, polishing the <sup>SIC</sup>substrate, implantation in the <sup>SIC</sup>substrate and/or laser processing the <sup>SIC</sup>substrate.

3. (Original) The method of Claim 1, wherein directly etching the second face of the silicon carbide substrate is carried out subsequent to singulation of the light emitting device from a wafer.

4. (Original) The method of Claim 1, wherein directly etching the second face of the silicon carbide substrate is carried out prior to singulation of the light emitting device from a wafer.

5. (Currently Amended) The method of Claim [[5]] 1, wherein the aqueous etch comprises an etch with KOH:K<sub>3</sub>Fe(CN)<sub>6</sub>.

6. (Original) The method of Claim 1, wherein directly etching the second face of the silicon carbide substrate further comprises etching a carbon-faced surface of the silicon carbide substrate.

7. (Original) The method of Claim 6, wherein the carbon-faced surface of the silicon carbide substrate comprises a carbon-faced surface of a sidewall of the <sup>Sic</sup>substrate.

8. (Original) The method of Claim 1, wherein directly etching the second face of the silicon carbide substrate further comprises etching a non-carbon-faced surface of the silicon carbide substrate.

9. (Original) The method of Claim 1, wherein directly etching the second face of the silicon carbide substrate comprises directly etching a surface oblique to the second face of the silicon carbide substrate.

10. (Currently Amended) A method of increasing light output of a light emitting [[device]] diode, comprising:  
etching a substrate of the light emitting [[device]] diode using an aqueous etch to at least partially remove a light absorption region of the substrate of the light emitting [[device]] diode.

11. (Original) The method of Claim 10, wherein the light absorption region corresponds to a region of the substrate damaged by processing the substrate in fabrication of the light emitting [[device]] diode.

12. (Original) The method of Claim 11, wherein the region of the substrate damaged by processing the substrate corresponds to a saw groove in the substrate.

13. (Original) The method of Claim 11, wherein the region of the substrate damaged by processing the substrate corresponds to a lapped, polished, implanted and/or laser processed region of the substrate.

14. (Original) The method of Claim 10, wherein the substrate comprises a silicon carbide substrate.

33. (Original) The method of Claim 24, wherein etching a substrate is carried out subsequent to singulation of the light emitting [[device]] diode.

34. (Original) The method of Claim 33, wherein the aqueous etch comprises etching with KOH:K<sub>3</sub>Fe(CN)<sub>6</sub>.

35. (Original) The method of Claim 34, wherein the aqueous etch is carried out for at least about 50 minutes.

36. (Original) The method of Claim 35, wherein the aqueous etch is carried out at a temperature of at least about 80 °C.

37. (Original) The method of Claim 34, wherein etching a substrate comprises directly etching the substrate.

~~38.~~ (Original) A method of fabricating a light emitting device, comprising: etching a silicon carbide substrate of the light emitting device using an aqueous etch to remove at least a portion of amorphous silicon carbide from a surface of the silicon carbide substrate of the light emitting device.

~~39.~~ (Original) The method of Claim 38, wherein the amorphous silicon carbide corresponds to a region of the <sup>Sic</sup>substrate damaged by processing the substrate in fabrication of the light emitting device.

~~40.~~ (Original) The method of Claim 39, wherein the region of the <sup>Sic</sup>substrate damaged by processing the substrate corresponds to a saw groove in the substrate.

~~41.~~ (Original) The method of Claim 39, wherein the region of the <sup>Sic</sup>substrate damaged by processing the substrate corresponds to a lapped, polished, implanted and/or laser processed region of the substrate.

~~42.~~ (Original) The method of Claim 38, wherein etching the substrate is carried out subsequent to singulation of the light emitting device. <sup>SIC</sup>

43. (Original) The method of Claim 38, wherein the aqueous etch comprises etching with KOH:K<sub>3</sub>Fe(CN)<sub>6</sub>.

44. (Original) The method of Claim 43, wherein the aqueous etch is carried out for at least about 50 minutes.

45. (Original) The method of Claim 43, wherein the aqueous etch is carried out at a temperature of at least about 80 °C.

46. (Original) The method of Claim 38, wherein etching a substrate comprises directly etching the substrate.

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47-56 (Cancelled)  
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